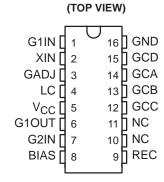
- Designed for Use With the TL851 in Sonar Ranging Modules Like the SN28827
- Digitally Controlled Variable-Gain Variable-Bandwidth Amplifier
- Operational Frequency Range of 20 kHz to 90 kHz
- TTL-Compatible
- Operates From Power Sources of 4.5 V to 6.8 V
- Interfaces to Electrostatic or Piezoelectric Transducers
- Overall Gain Adjustable With One External Resistor



N PACKAGE

NC - No internal connection

### description

The TL852 is an economical sonar ranging receiver integrated circuit for use with the TL851 control integrated circuit. A minimum of external components is required for operation, and this amplifier easily interfaces to Polaroid's 50-kHz electrostatic transducer. An external 68-k $\Omega$  ±5% resistor from BIAS to GND provides the internal biasing reference. Amplifier gain can be set with a resistor from G1IN to GADJ. Required amplifier gain will vary for different applications. Using the detect-level measurement circuit of Figure 1, a nominal peak-to-peak value of 230 mV input during gain step 2 is recommended for most applications. For reliable operation, a level no lower than 50 mV should be used. The recommended detect level of 230 mV can be obtained for most amplifiers with an R1 value between 5 k $\Omega$  and 20 k $\Omega$ 

Digital control of amplifier gain is provided with gain control inputs GCA, GCB, GCC, and GCD. These inputs must be driven synchronously (all inputs stable within 0.1  $\mu$ s) to avoid false receive output signals due to invalid logic counts. This can be done easily with the TL851 control integrated circuit. A plot showing relative gain for the various gain steps versus time can be seen in Figure 2. To dampen ringing of the 50-kHz electrostatic transducer, a 5-k $\Omega$  resistor from G1IN to XIN is recommended.

An external parallel combination of inductance and capacitance between LC and  $V_{CC}$  provides an amplifier with an externally controlled gain and Q. This not only allows control of gain to compensate for attenuation of signal with distance, but also maximizes noise and sidelobe rejection. Care must be taken to accurately tune the L-C combination at operating frequency or gain and Q will be greatly reduced at higher gain steps.

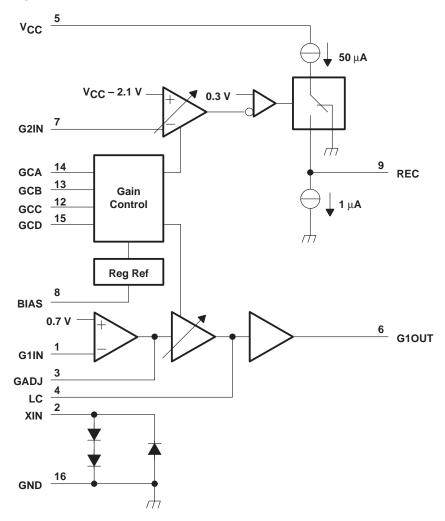
AC coupling between stages of the amplifier is accomplished with a 0.01-mF capacitor for proper biasing.

The receive output is normally held at a low level by an internal 1- $\mu$ A current source. When an input of sufficient amplitude is received, the output is driven alternately by the 1- $\mu$ A discharge current and a 50- $\mu$ A charging current. A 1000-pF capacitor is required from REC to GND to integrate the received signal so that one or two noise pulses will not be recognized.

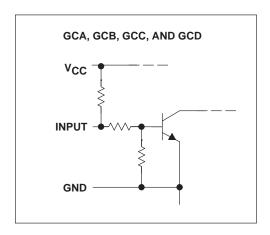
XIN provides clamping for the transformer secondary when used for transducer transmit drive as shown in Figure 4 of the SN28827 data sheet.

The TL852 is characterized for operation from 0°C to 40°C.

## functional block diagram



# schematic of gain control inputs





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# absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Voltage at any pin with respect to GND 0.5 V to 7 V
Voltage at any pin with respect to V <sub>CC</sub> – 7 V to 0.5 V
XIN input current (50% duty cycle) ±60 mA
Continuous power dissipation at (or below) 25°C free-air temperature (see Note 1) 1150 mW
Operating free-air temperature range – 40°C to 85°C
Storage temperature range – 65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds

<sup>†</sup> Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. This is a stress rating only, and functional operation of the device at these or any other conditions beyond those indicated in the recommended operating conditions section of this specification is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTE 1: For operation above 25°C, derate linearly at the rate of 9.2 mW/°C.

## recommended operating conditions

		MIN	MAX	UNIT
Supply voltage, V <sub>CC</sub>		4.5	6.8	V
High-level input voltage, VIH	GCA, GCB, GCC, GCD			\/
Low-level input voltage, V <sub>IL</sub>			0.6	V
Bias resistor between BIAS and GND			72	kΩ
Operating free-air temperature, T <sub>A</sub>			40	°C

# electrical characteristics over recommended ranges of supply voltage and operating free-air temperature (unless otherwise noted)

PARAMETER	TEST CONDITIONS		MIN TYP‡	MAX	UNIT
Input clamp valtage at VIN	I <sub>I</sub> = 40 mA I <sub>I</sub> = -40 mA			2.5	V
Input clamp voltage at XIN				- 1.5	1
Open-circuit input voltage at GCA, GCB, GCC, GCD	V <sub>CC</sub> = 5 V,	I <sub>I</sub> = 0	2.5		V
High-level input current, I <sub>IH</sub> , into GCA, GCB, GCC, GCD	V <sub>CC</sub> = 5 V,	V <sub>IH</sub> = 2 V	- 0.5		mA
Low-level input current, I <sub>IL</sub> , into GCA, GCB, GCC, GCD	V <sub>CC</sub> = 5 V,	V <sub>IL</sub> = 0		-3	mA
Raceive output current	$I_{G2IN} = -100 \mu A$ ,	V <sub>O</sub> = 0.3 V	1		μΑ
	$I_{G2IN} = 100 \mu A$ ,	$V_0 = 0.1 \text{ V}$	- 50		
Supply current, ICC				45	mA

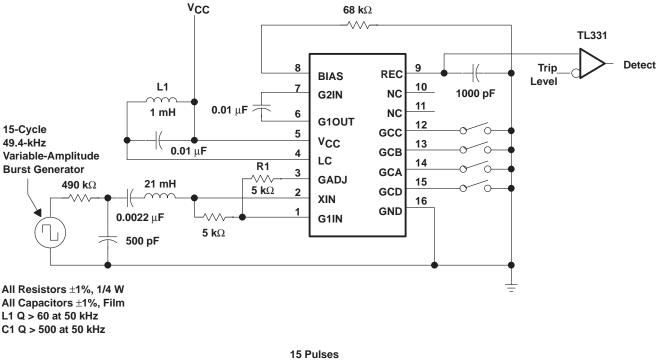
<sup>‡</sup> Typical values are at  $V_{CC} = 5 \text{ V}$  and  $T_A = 25^{\circ}\text{C}$ .



#### **APPLICATION INFORMATION**

### detect level versus gain step

Detect level is measured by applying a 15-cycle burst of 49.4 kHz square wave just after the beginning of the gain step to be tested. The least burst amplitude that makes REC reach the trip level is defined to be the detect level. System gain is then inversely proportional to detect level. See the test circuit in Figure 1.



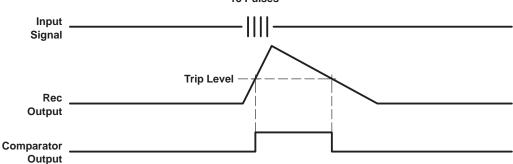


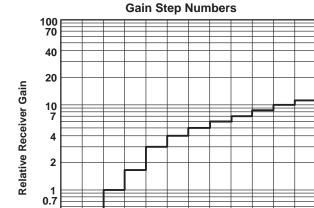
Figure 1. Detect-Level Measurement Circuit and Waveforms

## **APPLICATION INFORMATION**

#### **GAIN STEP TABLE**

GCD	GCC	GCB	GCA	STEP NUMBER
L	L	L	L	0
L	L	L	Н	1
L	L	Н	L	2
L	L	Н	Н	3
L	Н	L	L	4
L	Н	L	Н	5
L	Н	Н	L	6
L	Н	Н	Н	7
Н	L	L	L	8
Н	L	L	Н	9
Н	L	Н	L	10
Н	L	Н	Н	11

# Receiver Gain vs



0.4

0.1

0 1 2 3

Figure 2

4 5 6 7

**Gain Steps** 

8 9 10 11

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